

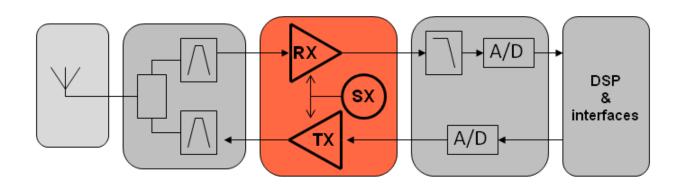
Aalto University School of Electrical Engineering

Department of Electronics and Nanoengineering

Integrated RF circuits Spring 2023

Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Transceiver Architectures and Concepts



- 1. Brief reminder on modulation and demodulation
- 2. Transmitter architectures
- 3. Receiver architectures
- 4. Gain, noise and nonlinearities

Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Modulation and Demodulation

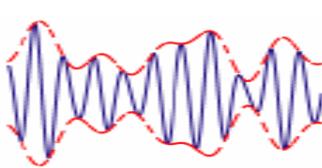
- Information is combined to or separated from the carrier wave
- Modulation schemes
 - Enables to transfer LF information at HF carrier

Core idea of radio comm

- Robust against noise and interference
- Spectrum efficient
- Analog systems: time-vary a single parameter of a general carrier wave

$$s(t) = A \cos(\omega t + \phi)$$

- AM
- FM
- PM



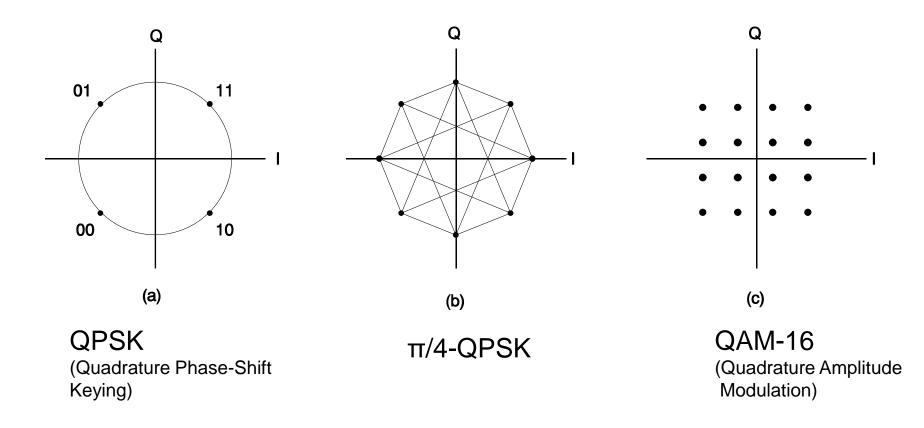
$OOK \approx Morse \ coding; \ Simplest "modulation"$



Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Modulation and Demodulation

 Modern communications systems utilize digital modulation schemes (modulating baseband signal is digital)



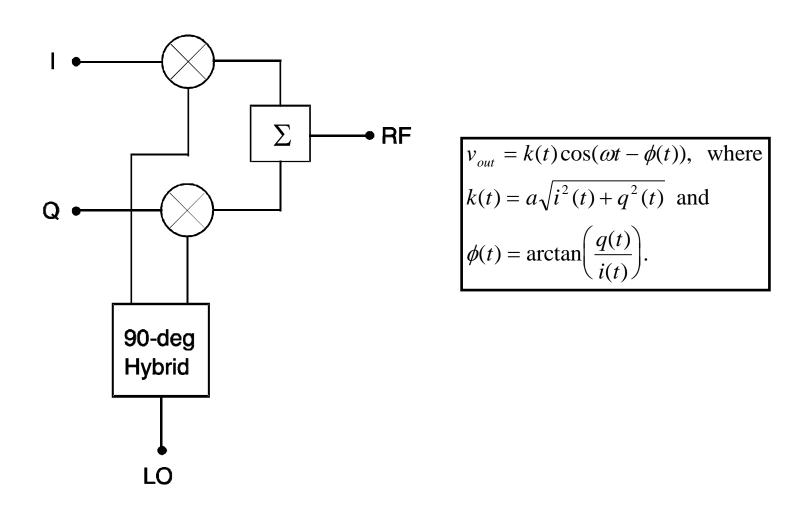
Department of Electronics and Nanoengineering

Integrated RF circuits Spring 2023

Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Aalto University School of Electrical Engineering

IQ-Modulator



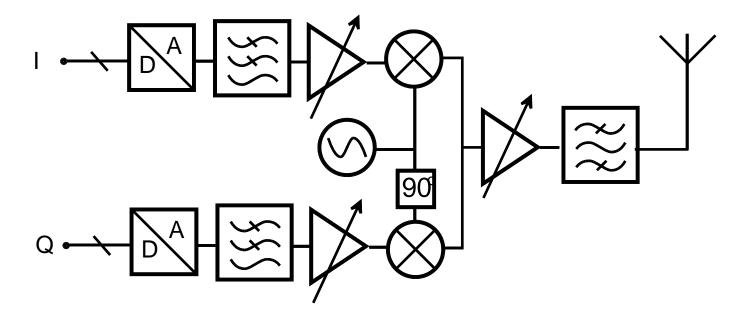


Department of Electronics and Nanoengineering

Integrated RF circuits Spring 2023

Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Direct-Conversion Transmitter

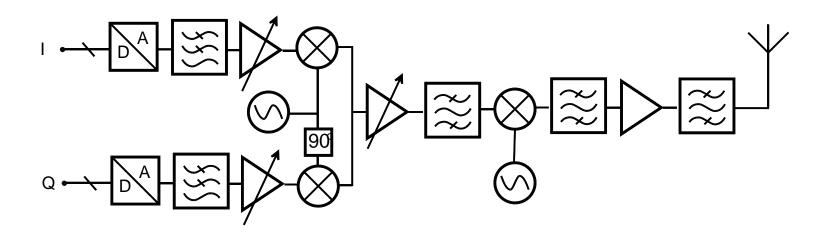


- High integration level
- LO at the same frequency as TX signal

Aalto University School of Electrical Engineering

Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Up-Converting Transmitter

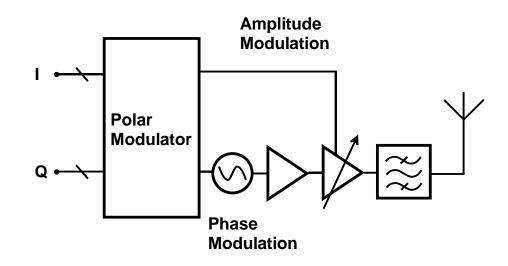


- Two or more up-conversions
- IQ-modulation at lower frequencies \rightarrow Improved performance
- BPFs difficult to integrate
 - High sideband suppression with BPF after second up-conversion



Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Polar Transmitter



- Phase and amplitude information separated in polar modulator (digital separation)
- Use of nonlinear PAs in transmitter \rightarrow Increased efficiency
- Bandwidth requirement of AM path increased compared to IQ-signal

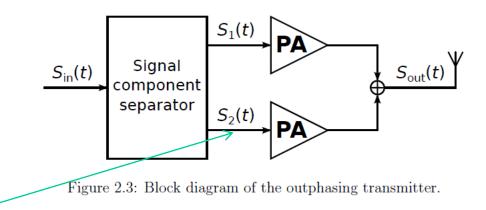


Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Out-Phasing aka LINC

LINC = linear amplification with nonlinear components

> NO Amplitude info = Non-linear PA ok!



similarly to the output of the polar transmitter. The two constant-envelope components are

$$S_1(t) = V_0 \cos(\omega t + \phi(t) + \theta(t))$$
(2.7)

$$S_2(t) = V_0 \cos(\omega t + \phi(t) - \theta(t)), \qquad (2.8)$$

where $\theta(t)$ is the outphasing angle. These signals are amplified with gain G and combined, resulting in the output signal

$$S_{\text{out}}(t) = GS_1(t) + GS_2(t).$$
 (2.9)

This sum is equal to

$$S_{\text{out}}(t) = 2GV_0 \cos(\omega t + \phi(t)) \cos(\theta(t)).$$
(2.10)

By choosing the outphasing angle to be

$$\theta(t) = \arccos \frac{E(t)}{V_0},\tag{2.11}$$

the output signal becomes the input signal amplified with gain 2G:

$$S_{\text{out}}(t) = 2GE(t)\cos(\omega t + \phi(t)).$$
(2.12)

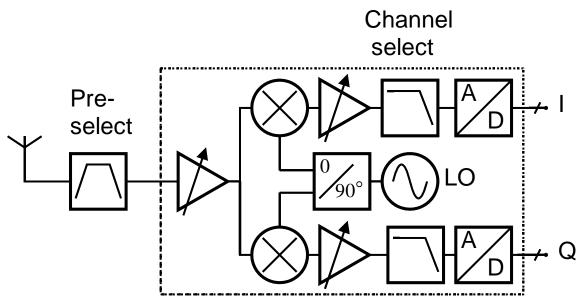
Aalto University School of Electrical Engineering

Department of Electronics and Nanoengineering

Integrated RF circuits Spring 2023

Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

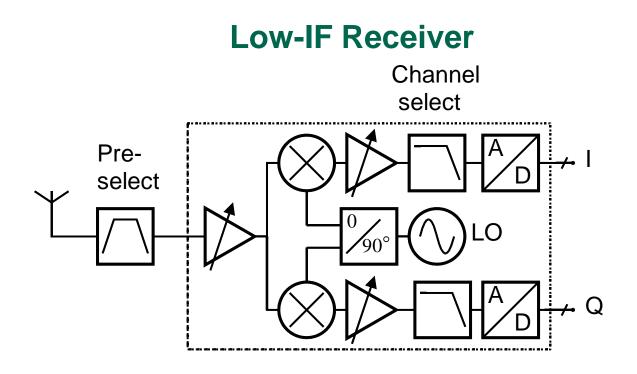
Direct-Conversion Receiver



- Signal demodulation is carried out at the signal frequency.
- Complexity of RF circuitry is minimized and receiver integration level maximized → Work-horse of modern RF ICs
- In the RF section two problems arise: LO radiation and DC-offsets.



Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

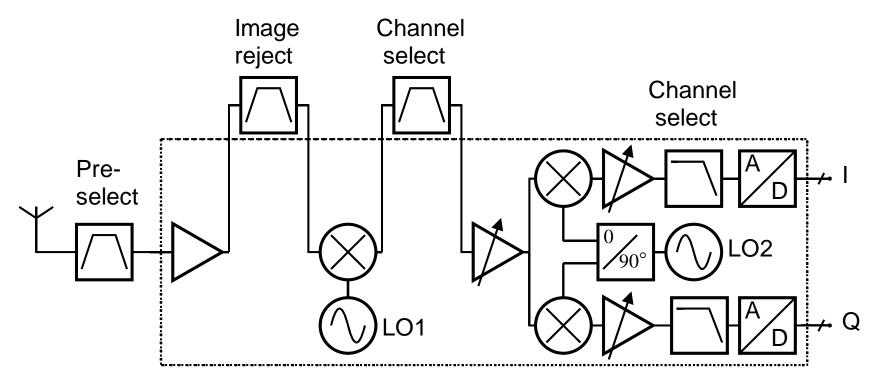


- Similar as direct conversion receiver
- Down-converted signal at low IF, e.g. 1 MHz
- No DC-offset problem
- Image must be suppressed sufficiently
- Wideband reception problematic



Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

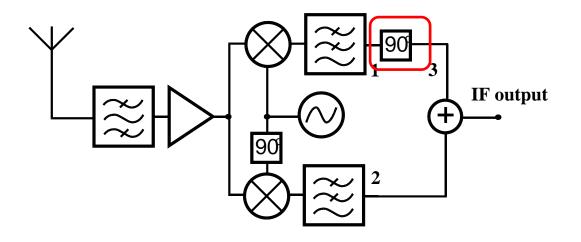
Superheterodyne Receiver



- Ability to achieve large dynamic range with moderate active elements,
- Good sensitivity and selectivity, "the best architecture"
- Requires high-quality filters \rightarrow Integration difficult (impossible with CMOS)

Aalto University School of Electrical Engineering

Image-reject Hartley Receiver

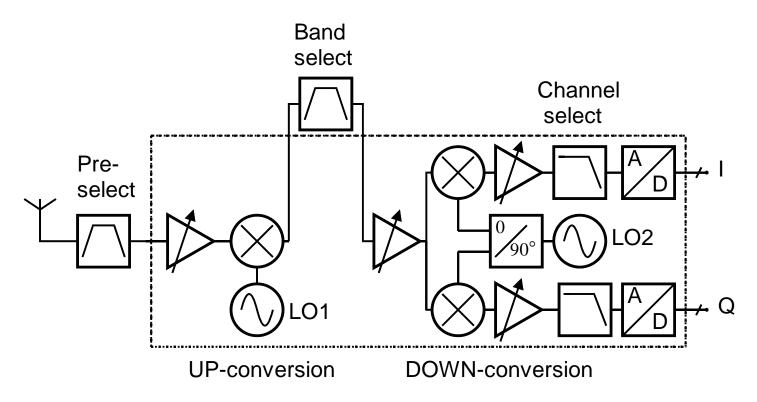


- No I/Q outputs
- Image frequency attenuated with 90 deg phase shift at IF
- Weaver architecture is an alternative to this one



Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Double-Conversion Receiver



- Very wideband RF signal -- LO is a challenge
- This architecture relieves SX requirements



Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

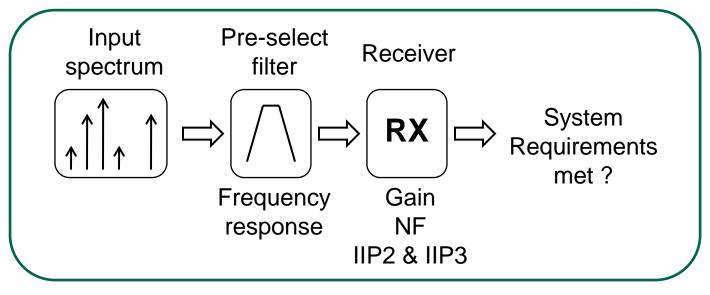
Why so many receiver architectures ?

- Wireless radio environment is very hostile; interfering signals!
- TX does not suffer from this challenge
- System standards dictate the needed features of the receiver
 - sensitivity, dynamic range, power, prize, size
- Manufacturing technology sets its own boundaries
- DCR is the present-day winner for moderate performance, low price radios, but keep other options in mind as well !!
- For instance, new performance requirements or a technology that enables new circuit techniques may alter the situation



Receiver Chain Design

RF IC designers need to carry out block design of transceivers, not only circuits!

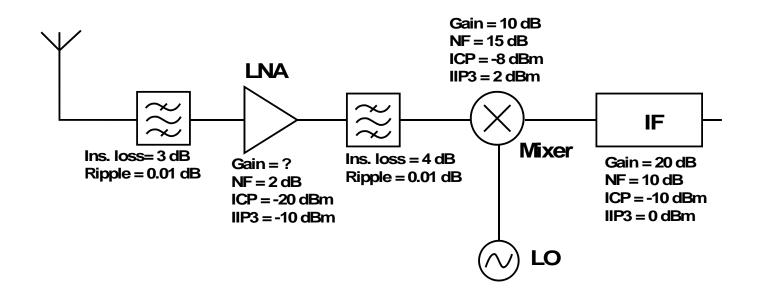


- Gain
- Noise Figure
- Nonlinear effects
 - Gain compression
 - Blockers
 - Intermodulation

Aalto University School of Electrical Engineering

Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Receiver Chain Design



Department of Electronics and Nanoengineering

Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Aalto University School of Electrical Engineering

Gain

Power gain is simply

$$G_p = \frac{P_{OUT}}{P_{IN}}$$

In classic RF engineering several definitions are used (operating power gain, transducer power gain, available power gain, unilateral transducer power gain), but they are rarely used in RF IC jargon.

Power gain is often problematic in RF IC design since impedance level of a node is not specifically defined and there is no impedance matching.

Voltage gain is

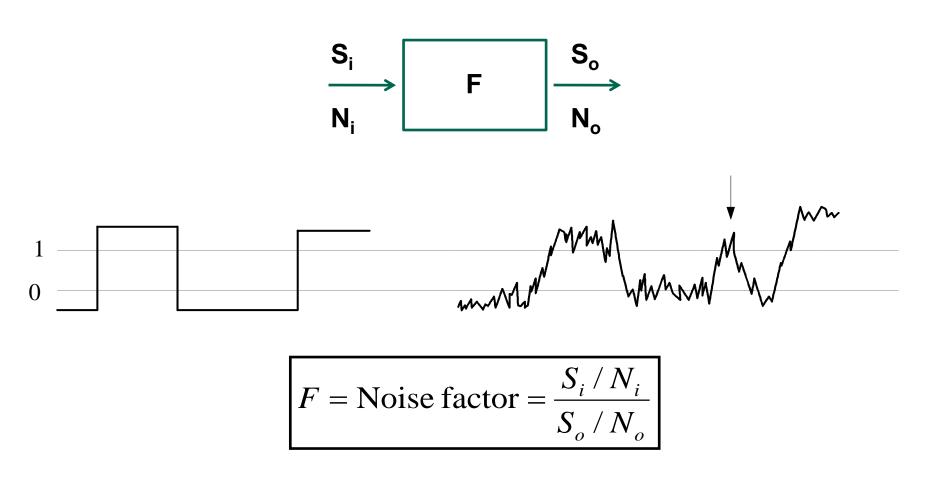
Aalto University School of Electrical Engineering

$$A_{v} = \frac{V_{out}}{V_{in}}$$

Some circuits (filters, some mixers) attenuate signals: Att = - Gain

Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Noise in Circuits



Noise Figure $NF = 10 \log$ (Noise factor)

Aalto University School of Electrical Engineering

Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Noise in Circuits (cont.)

$$F = \frac{S_i / N_i}{GS_i / N_o} = \frac{N_o}{GN_i}$$

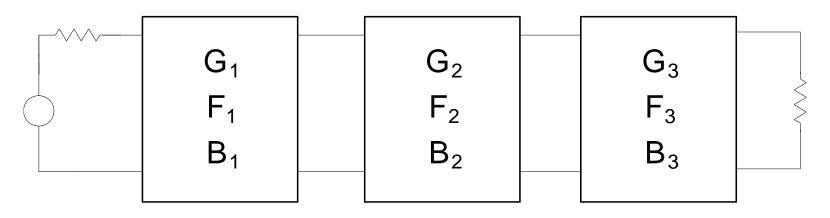
$$F = \frac{N_o}{GN_i} = \frac{G(N_i + N_a)}{GN_i} = 1 + \frac{N_a}{N_i}$$
no signal here!

- N_a = added noise generated by the circuit and referred to the input of the circuit
- N_i is defined to be the thermal noise of the generator resistor at the standard temperature $T_o=290$ K: $N_i = kT_oB$



Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

System Noise Figure



 $N_{A1} = (F_1 - 1)kTB_{1,3} \leftarrow \text{bandwidth through path } 1...3 = B_{tot}$ $N_{A2} = (F_2 - 1)kTB_{2,3} \leftarrow \text{bandwidth through path } 2...3$ $N_{A3} = (F_3 - 1)kTB_{3,3} \leftarrow \text{bandwidth through } 3$

$$N_{A,tot} = N_{A1} + \frac{N_{A2}}{G_1} + \frac{N_{A3}}{G_1 G_2}$$

$$F_{tot} = F_1 + \frac{F_2 - 1}{G_1} \frac{B_{2,3}}{B_{tot}} + \frac{F_3 - 1}{G_1 G_2} \frac{B_3}{B_{tot}}$$

Often, B is constant.

Aalto University School of Electrical Engineering

Department of Electronics and Nanoengineering

Integrated RF circuits Spring 2023

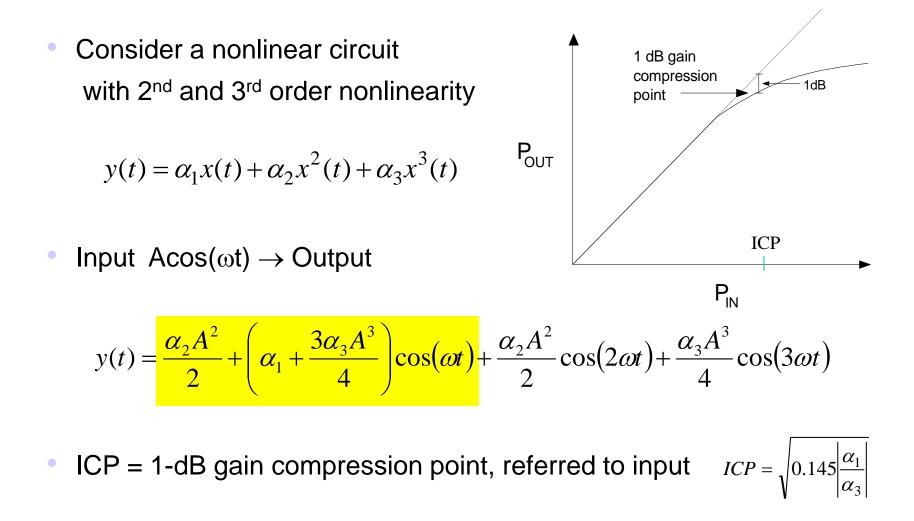
Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Nonlinear Circuit

• Nonlinear circuit generates a series of new frequencies

- Widely used specifications
 - gain compression
 - distortion (level of harmonics)
 - intermodulation
 - blocker resilience

Gain Compression



Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Aalto University School of Electrical Engineering

Level of Harmonics

• Nonlinear circuit with 2nd and 3rd order nonlinearity

$$y(t) = \alpha_1 x(t) + \alpha_2 x^2(t) + \alpha_3 x^3(t)$$

• Input Acos(ω t) \rightarrow Output

$$y(t) = \frac{\alpha_2 A^2}{2} + \left(\alpha_1 + \frac{3\alpha_3 A^3}{4}\right) \cos(\omega t) + \frac{\alpha_2 A^2}{2} \cos(2\omega t) + \frac{\alpha_3 A^3}{4} \cos(3\omega t)$$

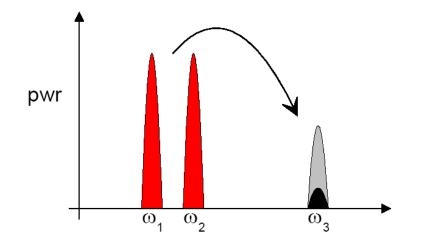
- Power at harmonic frequencies is widely used measure (THD) in low-frequency circuits
- IN RF circuits this is often a problematic measure
 - RF circuits are often frequency selective
 - Harmonics can be at very high frequencies making measurements difficult



Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Intermodulation

- In wireless applications modulated narrow band signals are used
- Nonlinearities cause different frequency components to mix with each other resulting in spreading of the spectrum
- Mechanism causing the spread is called intermodulation distortion
- The two-tone test is a simplified test more suitable for testing and simulation





Intermodulation

• Nonlinear circuit with 2nd and 3rd order nonlinearity

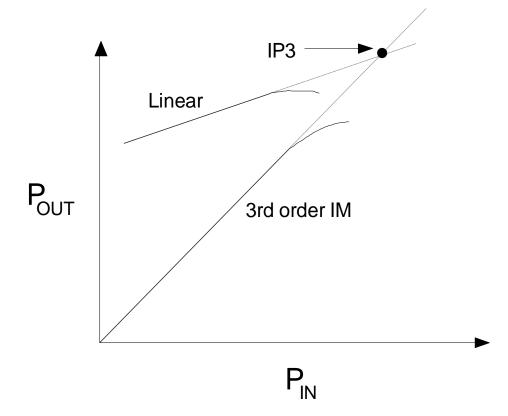
$$y(t) = \alpha_1 x(t) + \alpha_2 x^2(t) + \alpha_3 x^3(t)$$

• Input $A_1 \cos(\omega_1 t) + A_2 \cos(\omega_2 t) \rightarrow \text{Output}$ $v_{out}(t) = \frac{1}{2} \alpha_2 (A_1^2 + A_2^2) + \left(\alpha_1 A_1 + \alpha_3 \frac{3A_1^3 + 6A_1 A_2^2}{4} \right) \cos(\omega_1 t) + \left(\alpha_1 A_2 + \alpha_3 \frac{3A_2^3 + 6A_1^2 A_2}{4} \right) \cos(\omega_2 t)$ $+ \frac{1}{2} \alpha_2 A_1^2 \cos(2\omega_1 t) + \frac{1}{2} \alpha_2 A_2^2 \cos(2\omega_2 t) + \frac{1}{4} \alpha_3 A_1^3 \cos(3\omega_1 t) + \frac{1}{4} \alpha_3 A_2^3 \cos(3\omega_2 t)$ $+ \alpha_2 A_1 A_2 \left[\cos(\omega_1 t - \omega_2 t) + \cos(\omega_1 t + \omega_2 t) \right] + \frac{3}{4} \alpha_3 A_1^2 A_2 \cos(2\omega_1 t + \omega_2 t) + \frac{3}{4} \alpha_3 A_1 A_2^2 \cos(\omega_1 t + 2\omega_2 t)$ $+ \frac{3}{4} \alpha_3 A_1^2 A_2 \cos(2\omega_1 t - \omega_2 t) + \frac{3}{4} \alpha_3 A_1 A_2^2 \cos(2\omega_2 t - \omega_1 t)$

If ω_1 and ω_2 are close to each other then the third-order intermodulation products at $2\omega_1 - \omega_2$ and $2\omega_2 - \omega_1$ fall close to ω_1 and ω_2 , and they appear at reception band.



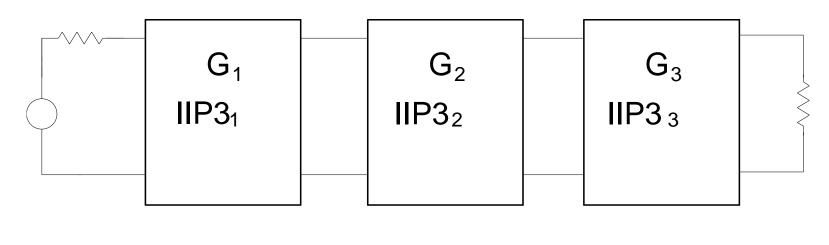
3rd Order Intermodulation Intercept Point (IIP3, OIP3)



- IIP2 and IIP3 are measure of device's nonlinearity: $IIP2 = \left| \frac{\alpha_1}{\alpha_2} \right|$ and $IIP3 = \sqrt{\frac{4}{3}} \left| \frac{\alpha_1}{\alpha_3} \right|$
- IIP3 ICP = 10 dB under these assumptions

Aalto University School of Electrical Engineering **Department of Electronics and Nanoengineering** Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

System IIP3



$$\frac{1}{iip3_{tot}} = \frac{1}{iip3_1} + \frac{g_1}{iip3_{12}} + \frac{g_1g_2}{iip3_3}$$

There are filters in the system, particularly at base-band:

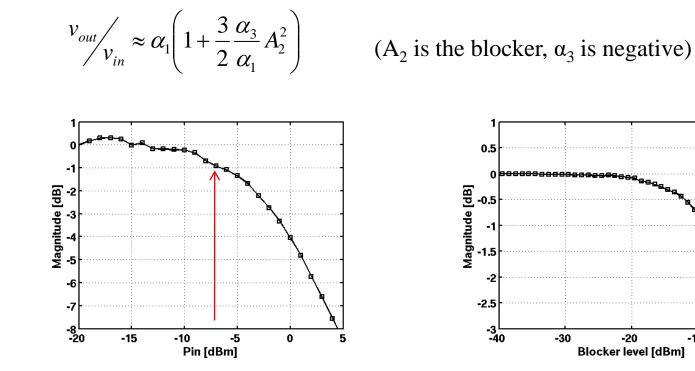
- Out-of-band IIP3 = intermodulation products falls to the stop-band of BB
- In-band IIP3 = intermodulation products falls to the pass-band of BB

Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

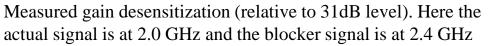
Aalto University School of Electrical Engineering

Blocker Resilience

"Blocker", "jammer" = A strong interfering signal that drives the receiver into / close to compression and the gain for the actual signal is reduced.



Measured input-referred gain compression (ICP) at 2.4 GHz (relative to 31dB level)



-10

-20

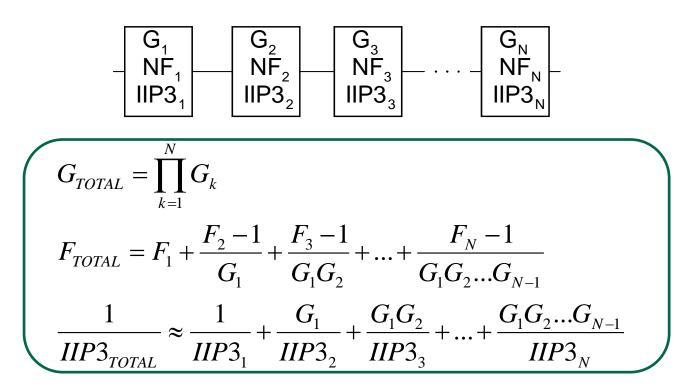


Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Integrated RF circuits Spring 2023

n

Chain Calculations



- NF of first stages dominate
- IIP3 requirement increases along the chain
- NF of attenuator: NF=ATT
- Assumption: power matched blocks, not exact for RF IC

Aalto University School of Electrical Engineering

Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Self-Learning Assignment 1

Objectives are to familiarize yourself with

- typical textbook level material on radio transceivers
- concepts
- architectures
- Aalto Library ebook-collections

You can find the assignment from

MyCourses / Assignments - SLA / Self-learning assignment 1

Return your answer as a pdf-file to Return Box in the same page



Department of Electronics and Nanoengineering Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

Next Meeting

Topics will be

- RF IC technologies
- High frequency properties of integrated devices
- RF IC specific devices: inductors and RF capacitors



Department of Electronics and Nanoengineering

Kari Stadius, Saeed Naghavi, Kimi Jokiniemi

This meeting will continue with

advices on homeworks and CAD exercise

at 14:15

Aalto University School of Electrical Engineering

Department of Electronics and Nanoengineering

Kari Stadius, Saeed Naghavi, Kimi Jokiniemi